



## Description

The DMN3300UQ-7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 30V$   $I_D = 5A$

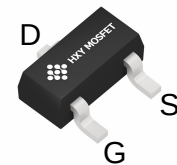
$R_{DS(ON)} < 42m\Omega$  @  $V_{GS}=10V$

## Application

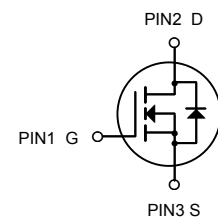
Battery protection

Load switch

Uninterruptible power supply



SOT-23



N-Channel MOSFET

## Package Marking and Ordering Information

| Product ID  | Pack   | Brand      | Qty(PCS) |
|-------------|--------|------------|----------|
| DMN3300UQ-7 | SOT-23 | HXY MOSFET | 3000     |

## Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

| Symbol          | Parameter                                        | Limit      | Unit          |
|-----------------|--------------------------------------------------|------------|---------------|
| $V_{DS}$        | Drain-Source Voltage                             | 30         | V             |
| $V_{GS}$        | Gate-Source Voltage                              | $\pm 12$   | V             |
| $I_D$           | Drain Current-Continuous                         | 5          | A             |
| $I_{DM}$        | Drain Current-Pulsed (Note 1)                    | 14.4       | A             |
| $P_D$           | Maximum Power Dissipation                        | 1          | W             |
| $T_J, T_{STG}$  | Operating Junction and Storage Temperature Range | -55 To 150 | $^{\circ}C$   |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 2) | 125        | $^{\circ}C/W$ |



### Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

| Symbol              | Parameter                                      | Conditions                                                                              | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------------------------|-----------------------------------------------------------------------------------------|------|------|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage                 | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                                              | 30   | ---  | ---  | V    |
| R <sub>DS(ON)</sub> | Static Drain-Source On-Resistance <sup>2</sup> | V <sub>GS</sub> =10V, I <sub>D</sub> =3A                                                | ---  | 33   | 42   | mΩ   |
|                     |                                                | V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A                                               | ---  | 38   | 48   |      |
| V <sub>GS(th)</sub> | Gate Threshold Voltage                         | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA                                | 0.4  | ---  | 1.2  | V    |
| I <sub>DSS</sub>    | Drain-Source Leakage Current                   | V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C                         | ---  | ---  | 1    | μA   |
|                     |                                                | V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C                         | ---  | ---  | 5    |      |
| I <sub>GSS</sub>    | Gate-Source Leakage Current                    | V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V                                              | ---  | ---  | ±100 | nA   |
| g <sub>fs</sub>     | Forward Transconductance                       | V <sub>DS</sub> =5V, I <sub>D</sub> =3A                                                 | ---  | 10.5 | ---  | S    |
| Q <sub>g</sub>      | Total Gate Charge (4.5V)                       | V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A                         | ---  | 4.6  | ---  | nC   |
| Q <sub>gs</sub>     | Gate-Source Charge                             |                                                                                         | ---  | 0.7  | ---  |      |
| Q <sub>gd</sub>     | Gate-Drain Charge                              |                                                                                         | ---  | 1.5  | ---  |      |
| T <sub>d(on)</sub>  | Turn-On Delay Time                             | V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, R <sub>G</sub> =3.3Ω<br>I <sub>D</sub> =3A | ---  | 1.6  | ---  | ns   |
| T <sub>r</sub>      | Rise Time                                      |                                                                                         | ---  | 42   | ---  |      |
| T <sub>d(off)</sub> | Turn-Off Delay Time                            |                                                                                         | ---  | 14   | ---  |      |
| T <sub>f</sub>      | Fall Time                                      |                                                                                         | ---  | 7    | ---  |      |
| C <sub>iss</sub>    | Input Capacitance                              | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz                                       | ---  | 310  | ---  | pF   |
| C <sub>oss</sub>    | Output Capacitance                             |                                                                                         | ---  | 49   | ---  |      |
| C <sub>rss</sub>    | Reverse Transfer Capacitance                   |                                                                                         | ---  | 35   | ---  |      |

### Diode Characteristics

| Symbol          | Parameter                                | Conditions                                                    | Min. | Typ. | Max. | Unit |
|-----------------|------------------------------------------|---------------------------------------------------------------|------|------|------|------|
| I <sub>S</sub>  | Continuous Source Current <sup>1,4</sup> | V <sub>G</sub> =V <sub>D</sub> =0V, Force Current             | ---  | ---  | 3.6  | A    |
| V <sub>SD</sub> | Diode Forward Voltage <sup>2</sup>       | V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C | ---  | ---  | 1.2  | V    |

Note :

1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

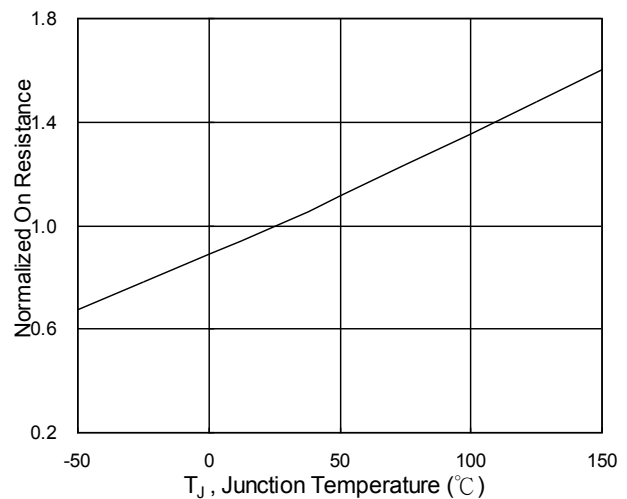
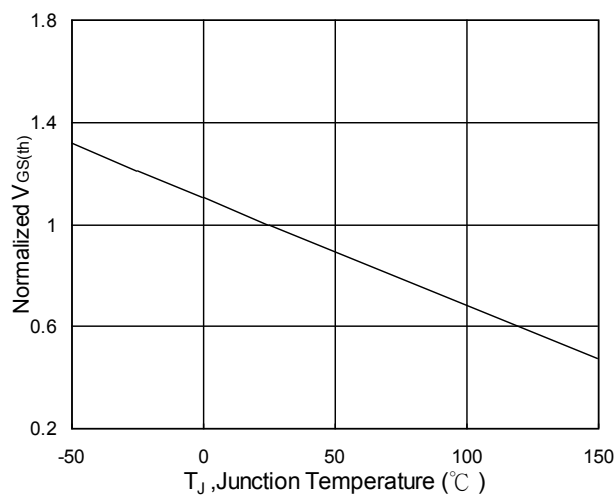
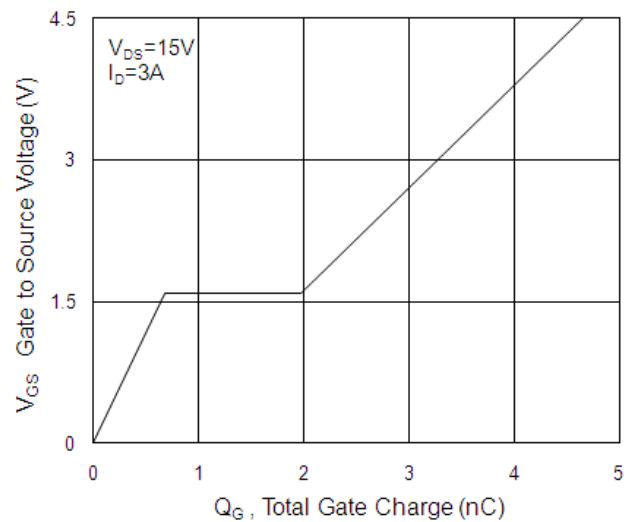
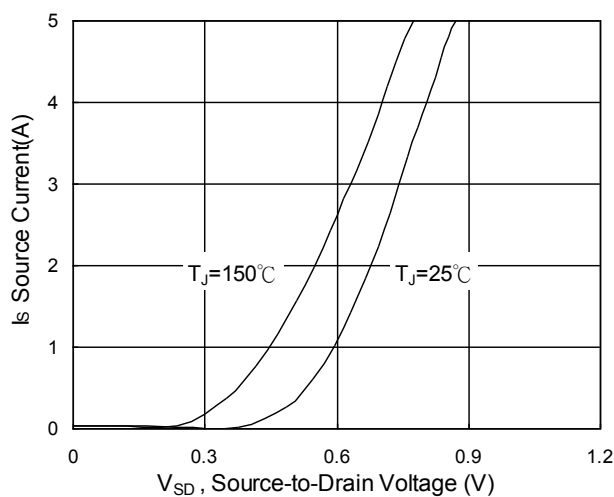
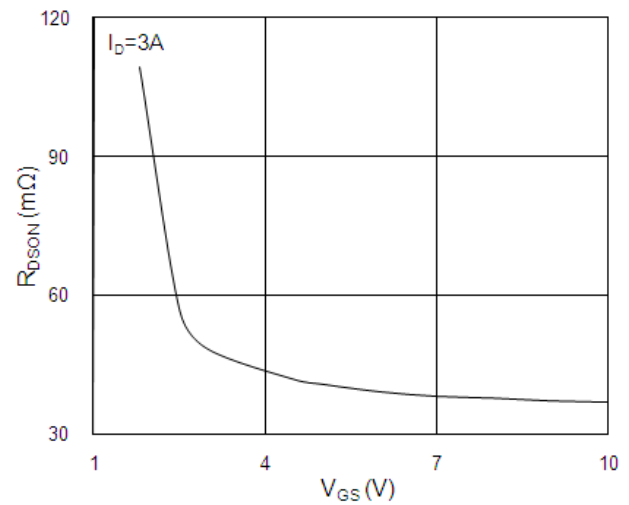
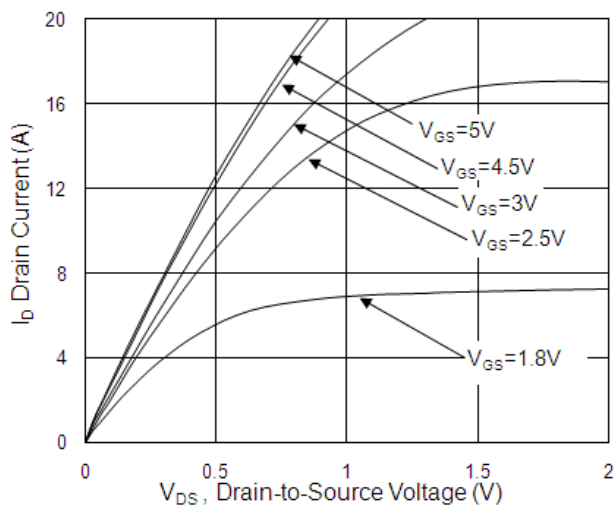
2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3.The power dissipation is limited by 150°C junction temperature

4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.



## Typical Characteristics



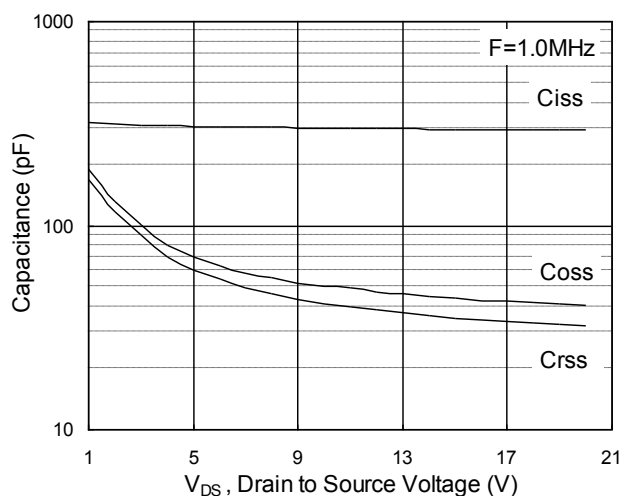


Fig.7 Capacitance

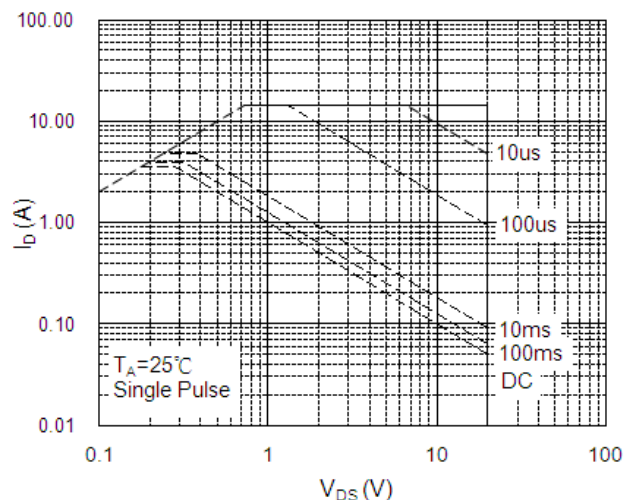


Fig.8 Safe Operating Area

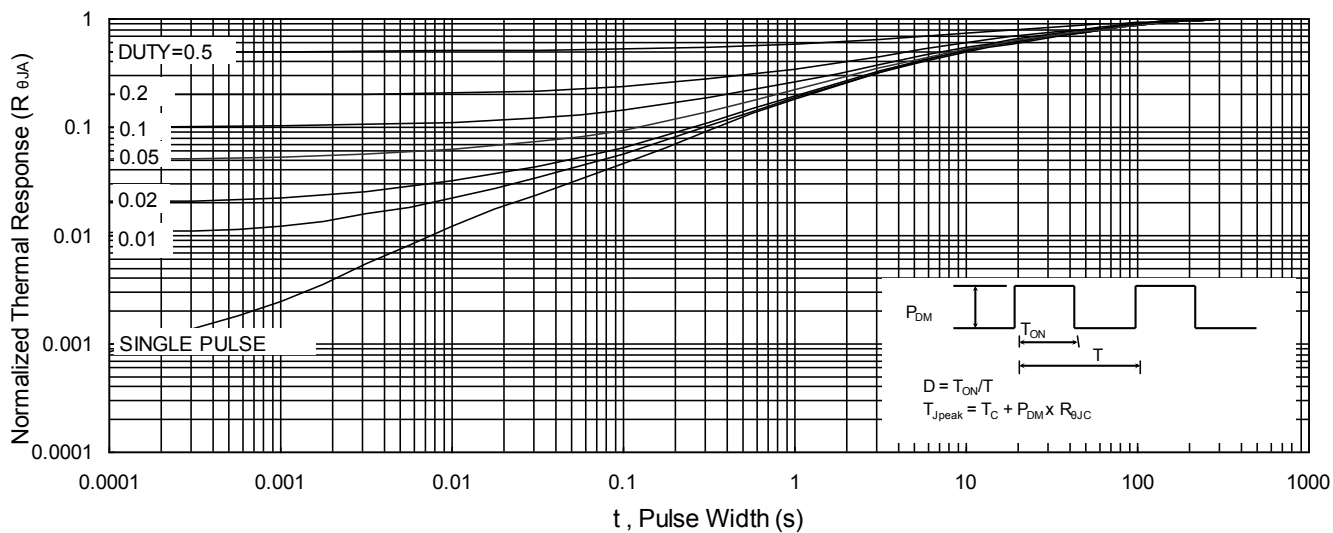


Fig.9 Normalized Maximum Transient Thermal Impedance

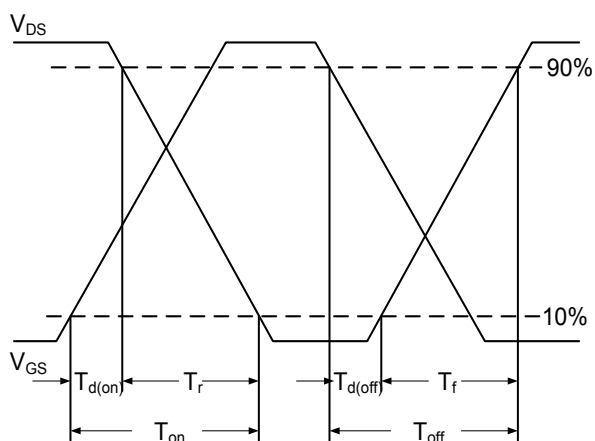


Fig.10 Switching Time Waveform

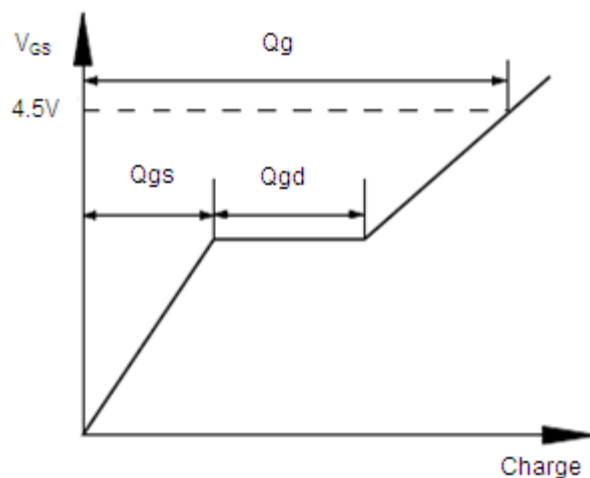
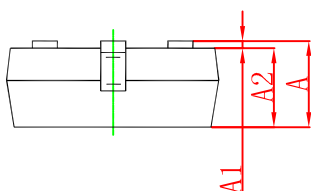
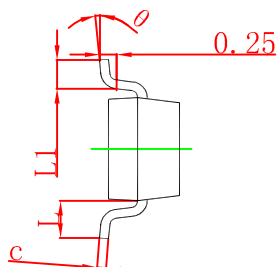
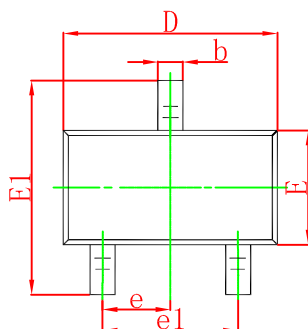


Fig.11 Gate Charge Waveform

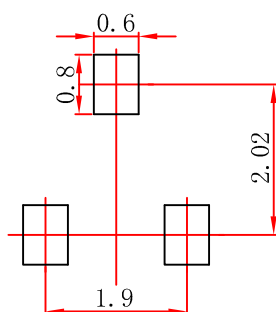


## SOT-23 Package Outline Dimensions



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 0.900                     | 1.150 | 0.035                | 0.045 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 0.900                     | 1.050 | 0.035                | 0.041 |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |
| c      | 0.080                     | 0.150 | 0.003                | 0.006 |
| D      | 2.800                     | 3.000 | 0.110                | 0.118 |
| E      | 1.200                     | 1.400 | 0.047                | 0.055 |
| E1     | 2.250                     | 2.550 | 0.089                | 0.100 |
| e      | 0.950 TYP                 |       | 0.037 TYP            |       |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |
| L      | 0.550 REF                 |       | 0.022 REF            |       |
| L1     | 0.300                     | 0.500 | 0.012                | 0.020 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |

## SOT-23 Suggested Pad Layout



Note:  
1. Controlling dimension: in millimeters.  
2. General tolerance:  $\pm 0.05\text{mm}$ .  
3. The pad layout is for reference purposes only.



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